

Supporting Information

Contact Evaluation of Penta-PdPSe/Graphene vdW Heterojunction: Tuning the Schottky

Barrier and Optical Properties

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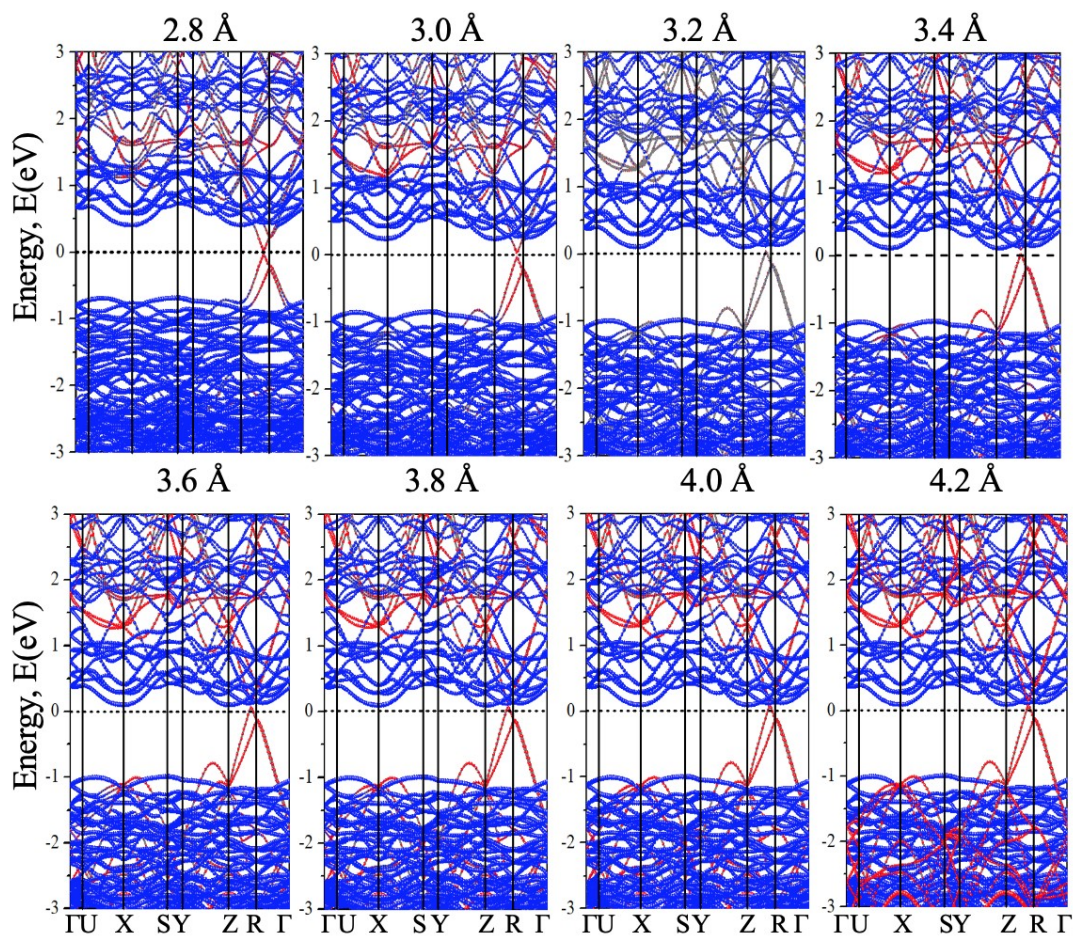


Figure S1: Band structures of PdPSe/Graphene with different interlayer spacing along the vertical direction.

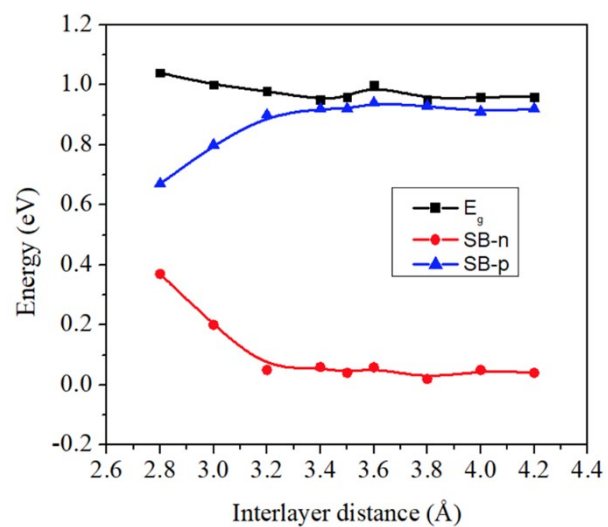


Figure S2: Schottky barrier for electrons (SB-n), holes (SB-p) and sum of Schottky barriers (E_g) as a function of interlayer distance for PdPSe/Graphene heterojunction.